

## **isc Silicon NPN Power Transistor**

### **DESCRIPTION**

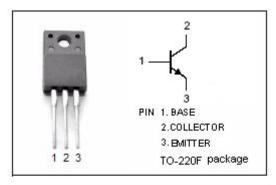
- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 550V(Min)
- · High Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

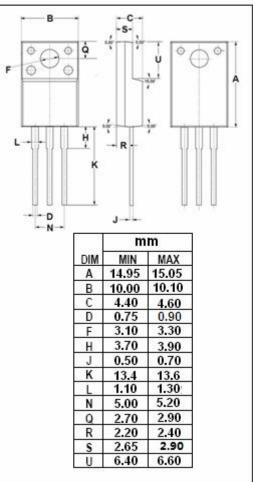
### **APPLICATIONS**

 Designed for switching regulator and general purpose applications.

## ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	900	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	550	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
lc	Collector Current-Continuous	3	А	
Ісм	Collector Current-Peak	6	Α	
I <sub>B</sub>	Base Current-Continuous	1.5	Α	
Pc	Collector Power Dissipation @Tc=25°C	30	W	
TJ	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature -55~150		$^{\circ}$	







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2SC4517

### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

Tj=25°C unless otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	550			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			0.5	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			1.2	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			100	μА			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			100	μА			
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	10		30				
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1MHz		35		pF			
f <sub>⊤</sub>	Current-Gain—Bandwidth Product	I <sub>E</sub> = -0.25A; V <sub>CE</sub> = 12V		6		MHz			
Switching Times									
ton	Turn-On Time				0.7	μS			
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 1A; I <sub>B1</sub> = 0.15A; I <sub>B2</sub> = -0.45A; V <sub>CC</sub> = 250V; R <sub>L</sub> = 250 Ω			4.0	μS			
t <sub>f</sub>	Fall Time				0.5	μS			

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